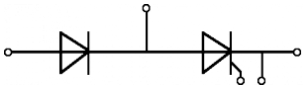
Thyristor/Diode module PSKH 1210M

$I_{T(RMS)}$ = 2x 1884 A
$I_{T(AV)}$ = 2x 1200 A
V_{RRM} = 800-1800 V

Preliminary Data Sheet



V_{RSM} V	V_{RRM} V	Type
900	800	PSKH 1010M/08
1100	1000	PSKH 1010M/10
1300	1200	PSKH 1010M/12
1500	1400	PSKH 1010M/14
1700	1600	PSKH 1010M/16
1900	1800	PSKH 1010M/18

Symbol	Test Conditions			Maximum Ratings	
$I_{T(RMS)}$	T_{VJ} = 125°C		half sine	1884	A
$I_{T(AV)}$	T_C = 85°C			1200	A
I_{TSM}	T_{VJ} = 125°C	t = 10 ms	half sine	34000	A
$\int i^2 dt$	T_{VJ} = 125°C	t = 10 ms	half sine	5480	$A^2 s*10^3$
$(di/dt)_{cr}$	T_{VJ} = 125°C	$t_r \leq$ 0,5µs	gate source 1,5A	200	A/µs
$(dv/dt)_{cr}$	T_{VJ} = 125°C	V_{DM}=2/3V_{DRM}		1000	V/µs
T_{VJ}				-40 ... + 125	°C
T_{VJM}				125	°C
T_{stg}				-40 ... + 125	°C
V_{ISOL}	50 HZ, RMS $I_{ISOL} \leq$ 1 mA	t = 1 min		min. 3000	V ~
M_d	Terminal connection torque		(M12)	14,0	Nm
	Mounting torque		(M8)	12,0	Nm
Weight	typ.			3660	g

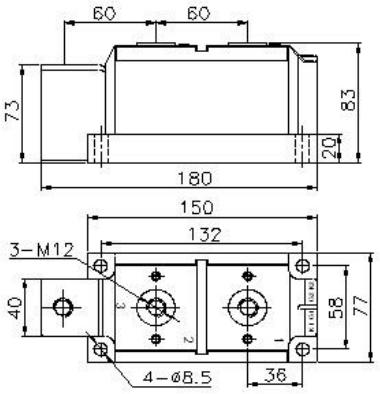
Symbol	Test Conditions			Characteristic Value	
I_{RRM} ; I_{DRM}	$V_R = V_{RRM}$ $V_D = V_{DRM}$	T_{VJ} = 125°C	≤	55	mA
V_{TM}	I_{TM} = 1884 A	T_{VJ} = 25°C	≤	1,76	V
V_{TO}	For power-loss calculations only			0,8	V
r_t	T_{VJ} = 125°C			0,09	mΩ
I_{GT}				30-200	mA
V_{GT}	V_A = 12 V I_A = 1 A	T_{VJ} = 25°C		1,0-3,0	V
I_H				20-200	mA
V_{GD}	V_{DM}=2/3V_{DRM}	T_{VJ} = 125°C		0,2	V
$R_{th(j-c)}$	Per chip; Single side cooled			0,031	°C /W

Features
- Isolated mounting base 3000V~
- Pressure contact technology with increased power cycling capability

Applications
- AC/DC Motor drives
- Various rectifiers
- DC supply for PWM inverter

Advantages
- Easy to mount
- Space and weight savings
- Improved temperature and power cycling capability

Package, style and outline
Dimensions in mm (1mm = 0.0394“)



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